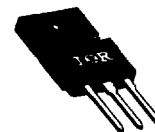


**TO-3P FullPak P-Channel**

Part Number	V(BR) <sub>DSS</sub> Drain-to-Source Breakdown Voltage (Volt)	R <sub>DS(on)</sub> On-State Resistance (Ohms)	I <sub>D</sub> Continuous Drain Current 25°C (Amps)	I <sub>D</sub> Continuous Drain Current 100°C (Amps)	R <sub>thJC</sub> Max Thermal Resistance (°C/W)	P <sub>d</sub> @T <sub>c</sub> = 25°C Max Power Dissipation (Watts)	Case Outline Number (1)	Case Style
IRFIP9140	-100	0.20	-15	-11	1.5	100	<b>H7</b>	<b>TO-247AC FullPak</b>
IRFIP9240	-200	0.50	-8.9	-5.6	1.5	83		



HEXSense



HEXSense Power MOSFETs provide the user with the ability to sense the current through the device by measuring a small proportion of the total drain current. The current-sensing is accomplished through the addition of the kelvin and current-sense connections providing for greater accuracy, wider bandwidths and cost-savings in current-mode applications.

**HEXSENSE N-Channel**

Part Number	V(BR) <sub>DSS</sub> Drain-to-Source Breakdown Voltage (Volt)	R <sub>DS(on)</sub> On-State Resistance (Ohms)	I <sub>D</sub> Continuous Drain Current 25°C (Amps)	I <sub>D</sub> Continuous Drain Current 100°C (Amps)	R <sub>thJC</sub> Max Thermal Resistance (°C/W)	P <sub>d</sub> @T <sub>c</sub> = 25°C Max Power Dissipation (Watts)	Nominal Sense Number	Case Outline Number (1)	Case Style
IRCZ24	60	0.10	17	12	2.5	60	820	<b>H8</b>	<b>TO-220 Hexsense</b>
IRCZ34	60	0.050	30	21	1.7	88			
IRCZ44	60	0.028	50	37	1.0	150			
IRC530	100	0.16	14	10	1.7	88			
IRC540	100	0.077	28	20	1.0	150			
IRC630	200	0.40	9.0	5.7	1.7	74			
IRC640	200	0.18	18	11	1.0	125			
IRC634	250	0.45	8.1	5.1	1.7	74			
IRC644	250	0.28	14	8.5	1.0	125			
IRC730	400	1.0	5.5	3.5	1.0	74			
IRC740	400	0.55	10	6.3	1.0	125			
IRC830	500	1.5	4.5	3.0	1.7	74			
IRC840	500	0.85	8.0	5.1	1.0	125			
<b>IRCP054</b>	60	0.014	70	64	0.65	230			



Part Number in bold indicates new product.  
(1) For case outline drawing see page O-2.